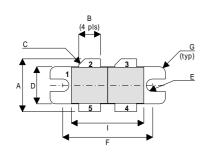
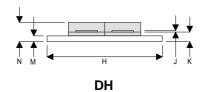


ROHS COMPLIANT METAL GATE RF SILICON FET

MECHANICAL DATA





PIN 1 SOURCE (COMMON) PIN₂ DRAIN 1 PIN₃ DRAIN 2 PIN 4 GATE 2

PIN 5 GATE 1

DIM	mm	Tol.	Inches	Tol.
Α	13.97	0.26	0.550	0.010
В	5.72	0.13	0.225	0.005
С	45°	5°	45°	5°
D	9.78	0.13	0.385	0.005
E	1.65R	0.13	0.065R	0.005
F	23.75	0.13	0.935	0.005
G	1.52R	0.13	0.060R	0.005
Н	30.48	0.13	1.200	0.005
I	19.17	0.26	0.755	0.010
J	0.13	0.02	0.005	0.001
K	2.54	0.13	0.100	0.005
M	1.52	0.13	0.060	0.005
N	5.08	0.50	0.200	0.020

GOLD METALLISED MULTI-PURPOSE SILICON DMOS RF FET 125W - 28V - 400MHz**PUSH-PULL**

FEATURES

- SIMPLIFIED AMPLIFIER DESIGN
- SUITABLE FOR BROAD BAND APPLICATIONS
- LOW C_{rss}
- SIMPLE BIAS CIRCUITS
- LOW NOISE
- HIGH GAIN 13 dB MINIMUM

APPLICATIONS

 HF/VHF/UHF COMMUNICATIONS from 1 MHz to 400 MHz

ABSOLUTE MAXIMUM RATINGS (T_{case} = 25° C unless otherwise stated)

P_{D}	Power Dissipation	350W
BV_DSS	Drain – Source Breakdown Voltage *	70V
BV_GSS	Gate – Source Breakdown Voltage *	±20V
I _{D(sat)}	Drain Current *	20A
T _{stg}	Storage Temperature	−65 to 150°C
Tj	Maximum Operating Junction Temperature	200°C

^{*} Per Side

Semelab PIc reserves the right to change test conditions, parameter limits and package dimensions without notice. Information furnished by Semelab is believed to be both accurate and reliable at the time of going to press. However Semelab assumes no responsibility for any errors or omissions discovered in its use. Semelab encourages customers to verify that datasheets are current before placing orders.

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ELECTRICAL CHARACTERISTICS (T_{case} = 25° C unless otherwise stated)

Parameter		Test Conditions		Min.	Тур.	Max.	Unit
	PER SIDE						
BV _{DSS}	Drain-Source	V _{GS} = 0	I _D = 100mA	70			V
	Breakdown Voltage			70			V
	Zero Gate Voltage	V _{DS} = 28V	V _{GS} = 0			4	A
IDSS	Drain Current					4	mA
I _{GSS}	Gate Leakage Current	V _{GS} = 20V	V _{DS} = 0			1	μА
V _{GS(th)}	Gate Threshold Voltage*	I _D = 10mA	$V_{DS} = V_{GS}$	1		7	V
9 _{fs}	Forward Transconductance*	V _{DS} = 10V	I _D = 4A	3.2			S
	TOTAL DEVICE						
G _{PS}	Common Source Power Gain	P _O = 125W		13			dB
η	Drain Efficiency	V _{DS} = 28V	$I_{DQ} = 1.6A$	50			%
VSWR	Load Mismatch Tolerance	f = 400MHz		20:1			_
PER SIDE							
C _{iss}	Input Capacitance	V _{DS} = 28V	$V_{GS} = -5V f = 1MHz$			240	pF
C _{oss}	Output Capacitance	V _{DS} = 28V	$V_{GS} = 0$ $f = 1MHz$			120	pF
C _{rss}	Reverse Transfer Capacitance	V _{DS} = 28V	$V_{GS} = 0$ $f = 1MHz$			10	pF

^{*} Pulse Test: Pulse Duration = 300 μs , Duty Cycle \leq 2%

HAZARDOUS MATERIAL WARNING

The ceramic portion of the device between leads and metal flange is beryllium oxide. Beryllium oxide dust is highly toxic and care must be taken during handling and mounting to avoid damage to this area.

THESE DEVICES MUST NEVER BE THROWN AWAY WITH GENERAL INDUSTRIAL OR DOMESTIC WASTE.

THERMAL DATA

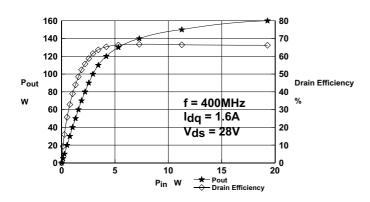
R _{THj-case}	Thermal Resistance Junction – Case	Max. 0.5° C / W
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E-mail: sales@semelab.co.uk Website: http://www.semelab.co.uk





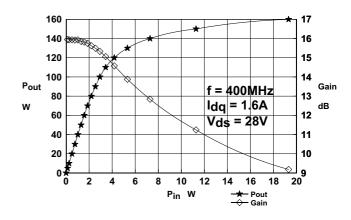
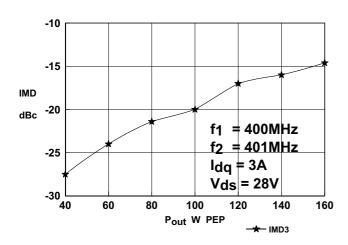


Figure 1 Power Output and Efficiency vs. Input Power

Figure 2 Power Output and Gain vs. Input Power



D1015UK OPTIMUM SOURCE AND LOAD IMPEDANCE

Frequency	Z _S	Z_{L}
MHz	Ω	Ω
400	1.7 - j0.1	2.7 - j1

Figure 3 IMD vs. Output Power

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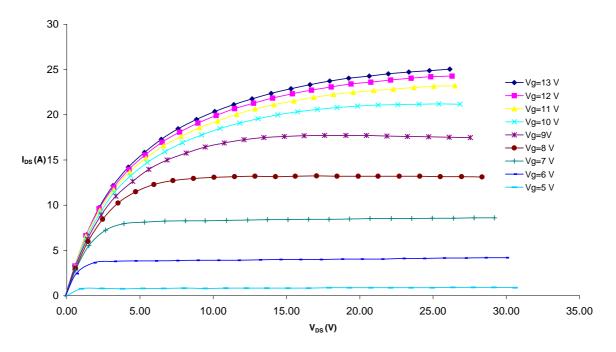


Figure 4 – Typical IV Characteristics.

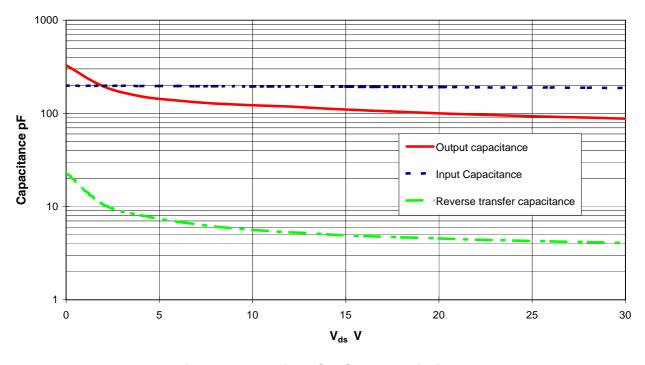


Figure 5 – Typical CV Characteristics.

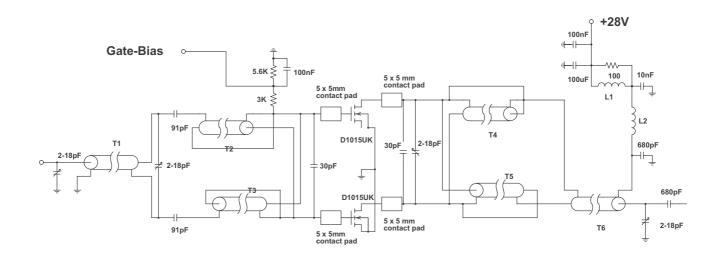
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D1015UK Test Fixture

- T1 12cm 50 ohm UT85 semi-rigid coax on ferrite core
- T2, 3 7.5cm 15 ohm UT85-15 semi-rigid coax
- T4,5 7cm 15 ohm UT85-15 semi-rigid coax
- T6 11cm 50 ohm UT85 semi-rigid coax on ferrite core
- L1 6.5 turns 25swg enamelled copper wire on Fair-Rite FT50B-43 core
- L2 6.5 turns 25swg enamelled copper wire, internal diameter

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